4,194,304-words  $\times$  1-bit High Speed Static Random Access Memory

# HITACHI

ADE-203-086G(Z) Rev. 8 Aug. 28, 1996

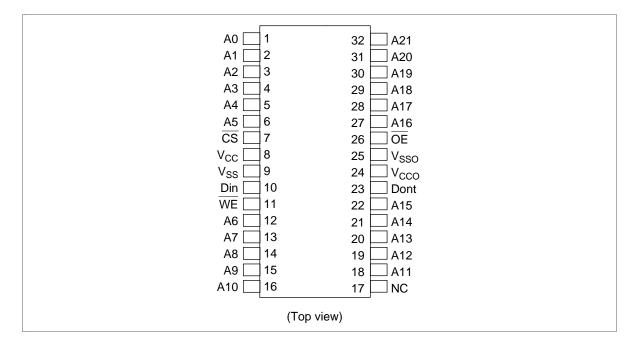
#### Features

- 4194304-words × 1 bit organization
- Directly TTL compatible input and output
- +5.0 V Single Supply
- Completely static memory
- No clock or timing strobe required
- Super fast access time: 15/20 ns (Max)
- Revolutional Pin Arrangement

## **Ordering Information**

Туре No.	Organization	Access time	Package
HM671400HJP-15		15 ns	400 mil 32 pin
HM671400HJP-20	$4M \times 1$	20 ns	Plastic SOJ (CP-32DB)

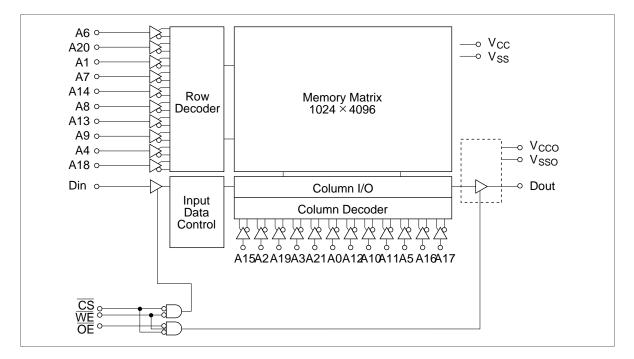
## **Pin Arrangement**



# **Pin Description**

Pin Name	Function
A0 to A21	Address Input
Din	Data Input
Dout	Data Output
WE	Write Enable
CS	Chip Select
ŌĒ	Output Enable
V <sub>cc</sub>	+5 V Power Supply
V <sub>cco</sub>	Output Buffer Power Supply
V <sub>sso</sub>	Output Buffer Ground
V <sub>ss</sub>	Ground
NC	Not Connect

## **Block Diagram**



#### **Function Table**

CS	WE	OE	Mode	Output	V <sub>cc</sub> Current
Н	X	Х	Not Selected	High Z	I <sub>SB</sub> , I <sub>SB1</sub>
L	Н	Н	Output Disable	High Z	I <sub>cc</sub> , I <sub>cc1</sub>
L	Н	L	Read	Data Out	I <sub>cc</sub> , I <sub>cc1</sub>
L	L	Н	Write	High Z	I <sub>cc</sub> , I <sub>cc1</sub>
L	L	L	Write	High Z	I <sub>cc</sub> , I <sub>cc1</sub>

## **Absolute Maximum Ratings**

Item	Symbol	Rating	Unit	
Supply Voltage *1	V <sub>cc</sub>	-0.5 to + 7.0	V	
Voltage on any pin relative to $V_{ss}^{*1}$	V <sub>T</sub>	-0.5 to V <sub>cc</sub> + 0.5	V	
Power dissipation	P <sub>T</sub>	1.0/1.5 *2	W	
Operating Temperature Range	Topr	0 to +70	°C	
Storage Temperature Range (with bias)	Tstg (Bias)	-10 to + 85	°C	
Storage Temperature Range	Tstg	–55 to + 125	°C	

Notes: 1. With respect to  $V_{SS} = V_{SSO}$ 

2.  $P_T = 1.5$  W is guaranteed under the minimum air flow exceeding 500 linear feet per minute.

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Under the dc and ac specifications shown in the Tables, this device is tested under the minimum transverse air flow exceeding 500 linear feet per minute.

# **Recommended DC Operating Conditions** ( $0^{\circ}C \le Ta \le 70^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit
Supply Voltage	$V_{cc}, V_{cco}$	4.5	5.0	5.5	V
	V <sub>ss</sub> , V <sub>sso</sub>	0.0	0.0	0.0	V
Input High Voltage	V <sub>IH</sub>	2.2		V <sub>cc</sub> + 0.5	V
Input Low Voltage	V <sub>IL</sub>	-0.5	_	0.8	V

**DC and Operating Characteristics** ( $V_{CC} = V_{CCO} = 5.0 \text{ V} \pm 10\%$ ,  $V_{SS} = V_{SSO} = 0 \text{ V}$ , Ta = 0 to +70°C)

			15		20		
Item	Symbol	Test Conditions	Min	Max	Min	Max	Unit
Input Leakage Current	ll <sub>u</sub> l	$V_{cc} = 5.5 V,$ $V_{iN} = 0 V to V_{cc}$		2		2	μA
Output Leakage Current	II <sub>LO</sub> I			10		10	μA
Operating Power Supply Current	I <sub>cc</sub>	$\overline{\text{CS}} = \text{V}_{\text{IL}}, \text{ I}_{\text{OUT}} = 0 \text{ mA}$		120	_	120	mA
Average Operating Current	I <sub>CC1</sub>	Min. cycle, $I_{OUT} = 0 \text{ mA}$		170		150	mA
Standby Power Supply Current	I <sub>SBAC</sub>	$\overline{\text{CS}} = V_{\text{IH}}$ Min. cycle		100		80	mA
		$\overline{CS} = V_{IH}$ All input fixed and $V_{IN} = V_{IH}$ or $V_{IL}$		20		20	mA
	I <sub>SB1</sub>	$\label{eq:constraint} \begin{split} \overline{CS} \geq V_{\rm CC} - 0.2 \ V \\ V_{\rm IN} \leq 0.2 \ V \ or \\ V_{\rm IN} \geq V_{\rm CC} - 0.2 \ V \end{split}$		10		10	mA
Output Low Voltage	V <sub>oL</sub>	I <sub>oL</sub> = 8 mA		0.4		0.4	V
Output High Voltage	V <sub>OH</sub>	$I_{OH} = -4 \text{ mA}$	2.4		2.4	_	V

AC Characteristics ( $V_{CC} = V_{CCO} = 5.0 \text{ V} \pm 10\%$ ,  $V_{SS} = V_{SSO} = 0 \text{ V}$ ,  $Ta = 0^{\circ}\text{C}$  to  $70^{\circ}\text{C}$ , unless otherwise noted.)

#### **Read Cycle**

		15		20			
Item	Symbol	Min	Max	Min	Max	Unit	
Read Cycle Time	t <sub>RC</sub>	15	_	20		ns	
Address Access Time	t <sub>AA</sub>		15		20	ns	
Chip Select Access Time	t <sub>ACS</sub>		15		20	ns	
Chip Selection to Output in Low Z	t <sub>LZ</sub> * <sup>1, *2</sup>	5		5		ns	
Output Enable to Output Valid	t <sub>oe</sub>		8		10	ns	
Output Enable to Output in Low Z	t <sub>oLZ</sub> *1, *2	2		2		ns	
Chip Deselection to Output in High Z	t <sub>HZ</sub> * <sup>1, *2</sup>	0	7	0	8	ns	
Output Hold from Address Change	t <sub>он</sub>	5		5		ns	

Notes: 1. This parameter is sampled and not 100\% tested.

2. Transition is measured ±200 mV from steady state voltage with specified loading in Load(B).

#### Write Cycle

		15		20			
Item	Symbol	Min	Max	Min	Max	Unit	
Write Cycle Time	t <sub>wc</sub> *1	15		20		ns	
Chip Selection to End of Write	t <sub>cw</sub>	12	_	15	_	ns	
Address Valid to End of Write	t <sub>AW</sub>	12		15		ns	
Address Setup Time	t <sub>AS</sub>	0		0		ns	
Write Pulse Width	t <sub>wP</sub>	12	_	15	_	ns	
Write Recovery Time	t <sub>wR</sub>	3		3		ns	
Data Valid to End of Write	t <sub>DW</sub>	8		10		ns	
Data Hold Time	t <sub>DH</sub>	0	_	0	_	ns	
Write Enable to Output in High Z	t <sub>wz</sub> * <sup>2, *3</sup>	0	7	0	8	ns	
Output Disable to Output in High Z	t <sub>OHZ</sub> * <sup>2, *3</sup>	0	7	0	8	ns	
Output Active from End of Write	t <sub>ow</sub> *2, *3	2	_	2	_	ns	

Notes: 1. All Write Cycle timings are referenced from the last valid address to the first transitioning address.

2. This parameter is sampled and not 100% tested.

3. Transition is measured ±200 mV from steady state voltage with specified with loading Load(B).

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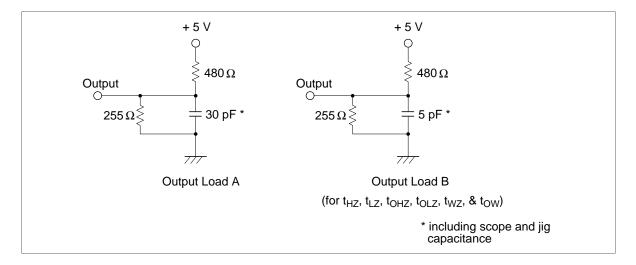
#### **Capacitance** (Ta = $25^{\circ}$ C, f = 1 MHz)

Item	Symbol	Max	Unit	Test Condition
Input Capacitance	C <sub>IN</sub> *	6	pF	$V_{IN} = 0 V$
Output Capacitance	C <sub>OUT</sub> *	8	pF	V <sub>OUT</sub> = 0 V

Note: This parameter is sampled and not 100% tested.

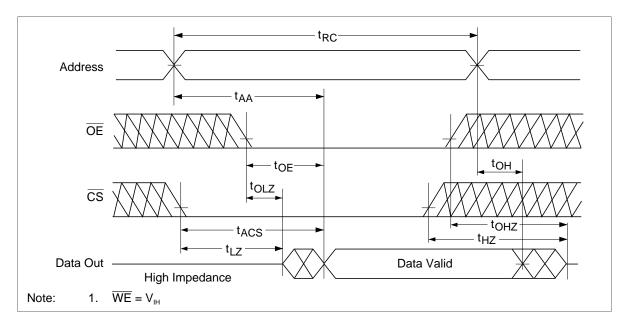
#### **AC Test Conditions**

- Input pulse levels:  $V_{ss}$  to 3.0 V
- Input timing reference levels: 1.5 V
- Output Load: See figure
- Input rise and fall times: 4 ns
- Output reference levels: 1.5 V

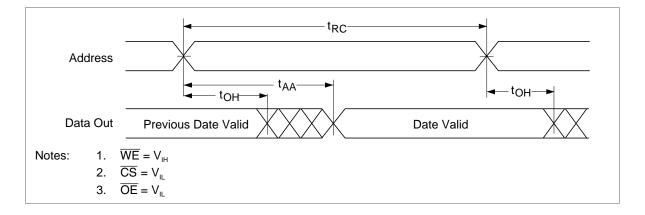


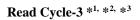
# **Timing Waveforms**

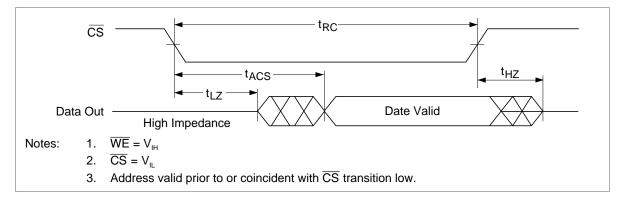
#### Read Cycle-1 \*1



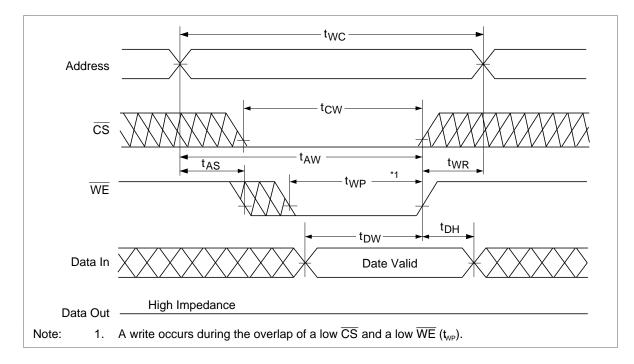
Read Cycle-2 \*<sup>1, \*2, \*3</sup>

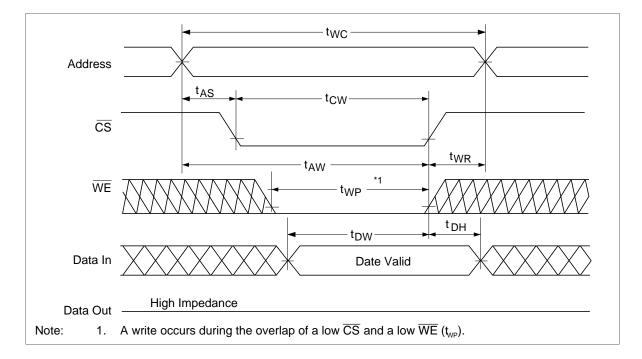




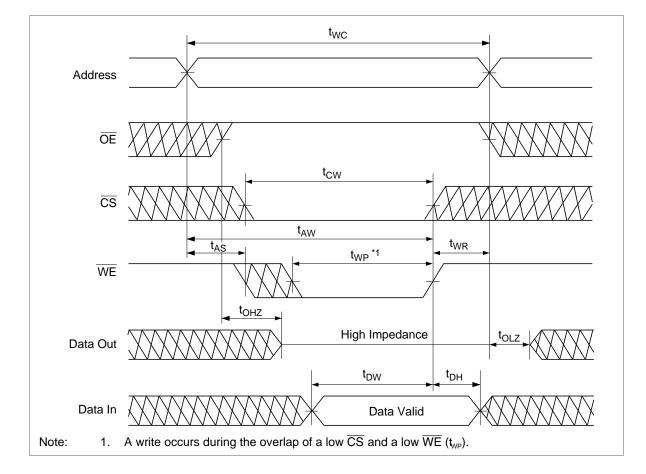


Write Cycle-1 \*<sup>1</sup> ( $\overline{OE}$  = H,  $\overline{WE}$  Controlled)

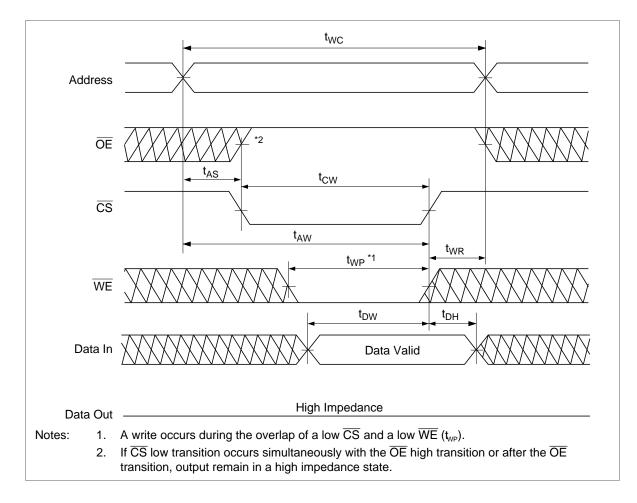




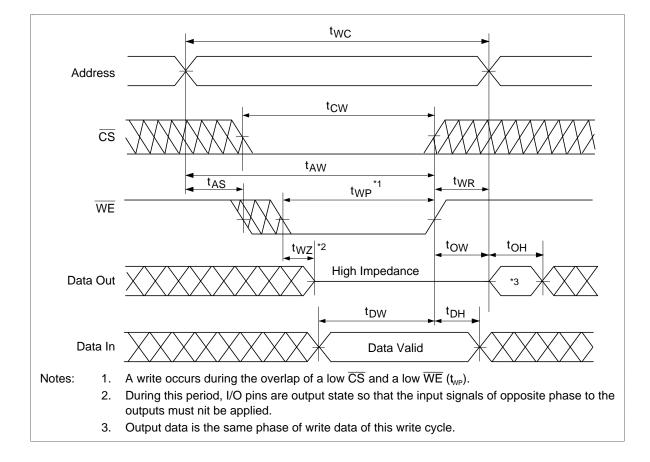
Write Cycle-2  $*^1$  ( $\overline{OE}$  = H,  $\overline{CS}$  Controlled)



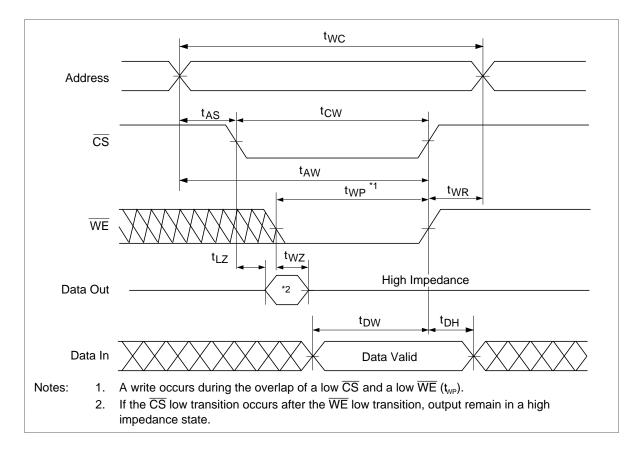
Write Cycle-3  $*^1$  ( $\overline{OE}$  = Clocked,  $\overline{WE}$  Controlled)



Write Cycle-4  $*^{1}$ ,  $*^{2}$  ( $\overline{OE}$  = Clocked,  $\overline{CS}$  Controlled)



Write Cycle-5 \*<sup>1,</sup> \*<sup>2,</sup> \*<sup>3</sup> ( $\overline{OE} = L$ ,  $\overline{WE}$  Controlled)

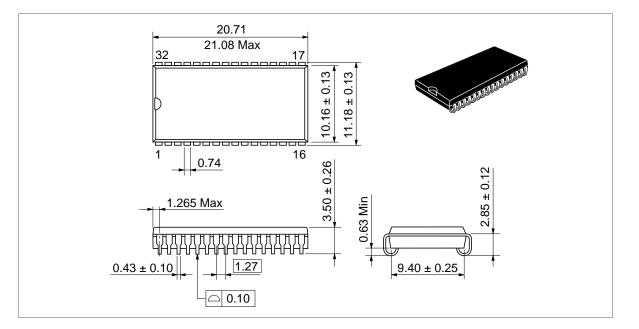


Write Cycle-6 \*<sup>1,</sup> \*<sup>2</sup> ( $\overline{OE}$  = L,  $\overline{CS}$  Controlled)

# **Package Dimension**







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